

EPITAXIAL GROWTH METHOD

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ABSTRACT OF THE DISCLOSURE

In accordance with the invention, a MOSFET includes a well, a channel formed in the well, a high K layer overlying the channel, a buffer layer overlying the high k layer, a gate overlying the buffer layer, a blocking layer overlying the gate and two source/drain regions. In some embodiments the gate and the source/drain regions are silicon germanium.

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